Abstracts

Low-Voltage High-Performance Silicon RF Power Transistors

M. Versleijen, R. Dekker, W.V.D. Einde and A. Pruijmboom. "Low-Voltage High-Performance Silicon RF Power Transistors." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 563-566.

The high-frequency power performance of mounted discrete silicon bipolar transistors, that have been optimised for low-voltage application, has been evaluated. At 1.8GHz and 3.5V a power gain of 14dB and a power-added efficiency of 60% at an RF power density of 1W/mm emitter length have been measured. These results demonstrate that also at low supply voltages silicon BJTs have excellent power amplifying capabilities.

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